

PHASE CHANGEABLE MEMORY DEVICES HAVING REDUCED
CELL AREAS AND METHODS OF FABRICATING THE SAME

ABSTRACT

5 Phase changeable memory devices include an integrated circuit substrate and first and
second storage active regions on the integrated circuit substrate. The first and second storage
active regions have a first width and a second width, respectively. A transistor active region
on the integrated circuit substrate is between the first and second active regions, the first and
seconds widths being less than a width of the transistor active region.

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